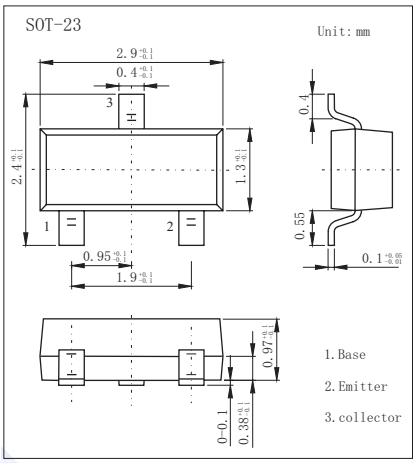
PNP Transistors
2SB1197 (2SB1197K)



■ Features

- Low $V_{CE(sat)}$.$V_{CE(sat)}$ ≤ -0.5V（I_C / I_B= -0.5A / -50mA）.
- I_C = -0.8A.
- PNP silicon transistor

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-40	V
Collector-emitter Voltage	V_{CEO}	-32	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector power dissipation	P_C	0.2	W
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltag	V_{CBO}	I_C = -50 μ A	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C = -1mA	-32			V
Emitter-base breakdown voltage	V_{EBO}	I_E = -50 μ A	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -20V			-0.5	μ A
Emitter cutoff current	I_{EBO}	V_{EB} = -4V			-0.5	μ A
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -0.5A , I_B = -50mA			-0.5	V
DC current transfer ratio	h_{FE}	V_{CE} = -3V , I_C = -100mA	120		390	
Output Capacitance	C_{ob}	V_{CB} = -10V , I_E = 0A , f = 1MHz		12	30	pF
Transition frequency	f_T	V_{CE} = -5V , I_E = 50mA , f = 100MHz		200		MHz

■ h_{FE} Classification

Type	2SB1197/K-Q	2SB1197/K-R
Range	120-270	180-390
Marking	AHQ	AHR

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■ Typical Characterisitics